

# Curvature-dependent reactivity of graphene for storage applications

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Graphene's strength and extreme flexibility allow sustained ripples in a wide range of amplitudes and wavelengths [1]. Ripples produce a modulation of the local curvature, which is strongly correlated with the stability of chemisorbed hydrogen atoms [2]. Curvature induced local pyramidalisation, i.e. pushing a carbon site towards the sp<sup>3</sup> configuration, contributes to the increase of graphene's reactivity [3]. Thus, the functionalization of curved graphene with hydrogen, or other adatoms, gives the possibility to tune its chemical and adsorption properties for storage and other applications [4].

While atomic hydrogen adhesion is a spontaneous process with a very small barrier, molecular hydrogen (H<sub>2</sub>) chemisorption process is characterized by a barrier high on the order of ~1.5eV/atom [5], making the kinetics of loading very slow. Moreover, H tends to stick onto convexities [2,5] and to detach from concavities on the curved graphene. In this work, we address the H<sub>2</sub>/graphene interaction useful for H-storage applications [4] as well as for the general understanding of graphene morphology/reactivity relationship. We propose that curvature manipulation could be used to improve the adhesion kinetics. To this aim, we perform a systematic density

functional theory (DFT) based study to evaluate the dependence of chemi(de)sorption barriers on curvature. We use different density functionals and dispersion corrections to DFT [6] on the model systems with various levels of corrugation generated by lateral compression of the isolated sheet [3], chosen to approximate the symmetry of natural rippling of graphene grown on SiC. We evaluate the chemi(de)sorption profiles by means of nudged elastic band technique [7] with and without effects of an external electric field to estimate the levels of curvature needed to use this effect in a real device [8]. An electric field orthogonal to the graphene sheet is likely to enhance the effect of curvature [9]. Calculations are ongoing.

## References

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